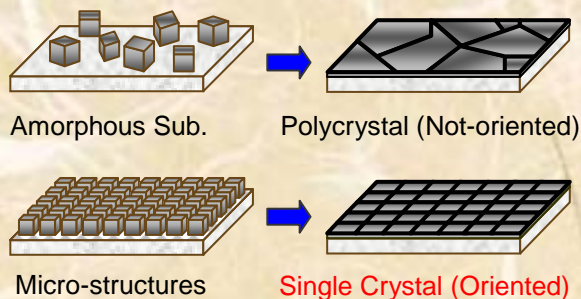


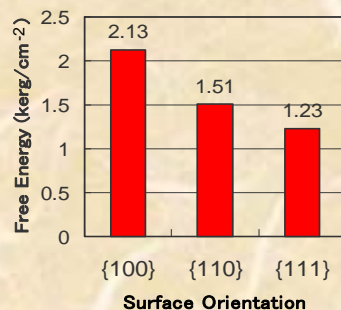
# Lateral Graphoepitaxy of Germanium Controlled by Microholes on SiO<sub>2</sub> Surface

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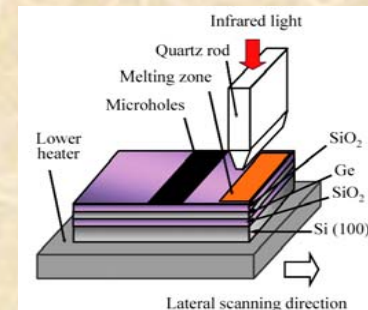
## 1. Graphoepitaxy



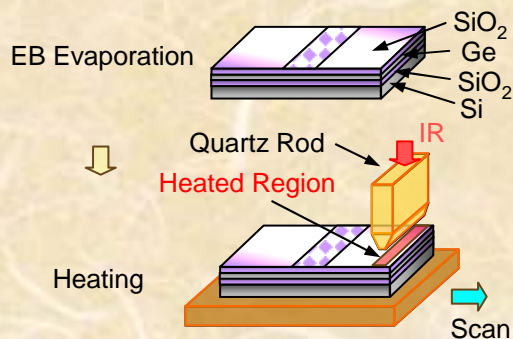
## 2. Gibbs Surface Free Energy (Si)



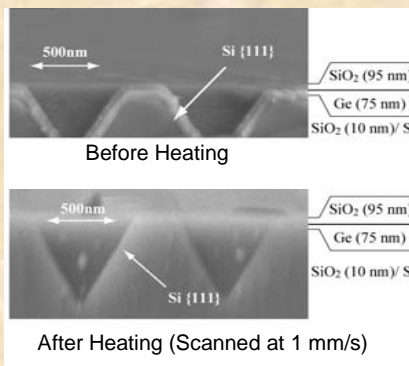
## 3. Fabrication Apparatus



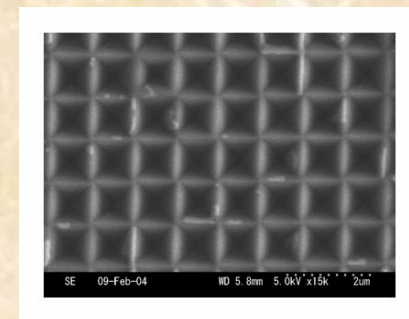
## 4. Fabrication Process



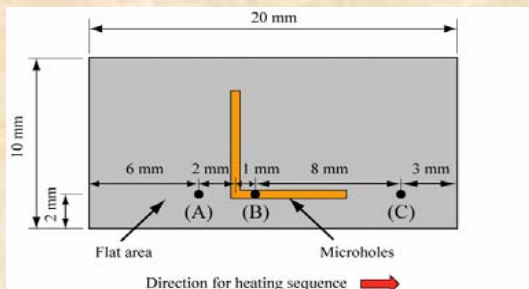
## 5. SEMs of Cross-sectional Views



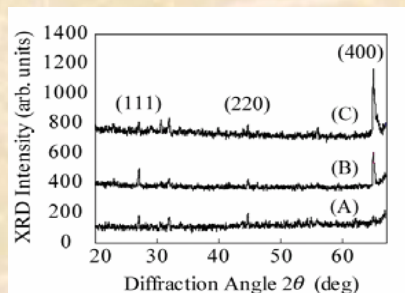
## 6. SEM of Top View after Heating Process



## 7. Measured Points



## 8. X-Ray Diffraction



## 9. Summary

Periodic {111} Planes

Thinner Layers than Critical Thickness



Control of Ge Orientation